

# **Isc N-Channel MOSFET Transistor**

## IPA60R460CE

#### FEATURES

- With TO-220F package
- · Low input capacitance and gate charge
- · Low gate input resistance
- Reduced switching and conduction losses
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



## APPLICATIONS

Switching applications

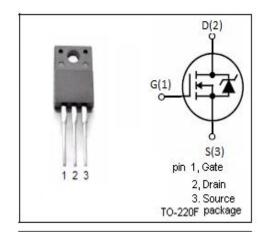


## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage	600	V
V <sub>GSS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous @Tc=25℃ (V <sub>GS</sub> at 10V) Tc=100℃	9.1 5.7	А
I <sub>DM</sub>	Drain Current-Single Pulsed	26	А
P <sub>D</sub>	Total Dissipation @T <sub>C</sub> =25℃	30	W
Tj	Max. Operating Junction Temperature	-40~150	$^{\circ}\!\mathbb{C}$
T <sub>stg</sub>	Storage Temperature	-40~150	${\mathbb C}$

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	4.2	°C/W
Rth(ch-a)	Channel-to-ambient thermal resistance	80	°C/W



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	1 3		m	
	DIM	MIN		
	Α		MAX 15.05	
	A B	MIN 14.95 10.00	MAX	
	A B C	MIN 14.95 10.00 4.40	MAX 15.05 10.10 4.60	
	B C D	MIN 14.95 10.00 4.40 0.75	MAX 15.05 10.10 4.60 0.90	
	A B C D	MIN 14.95 10.00 4.40 0.75 3.10	MAX 15.05 10.10 4.60 0.90 3.30	
	A B C D F	MIN 14.95 10.00 4.40 0.75 3.10 3.70	MAX 15.05 10.10 4.60 0.90 3.30 3.90	
	A B C D F H	MIN 14.95 10.00 4.40 0.75 3.10 3.70 0.50	MAX 15.05 10.10 4.60 0.90 3.30 3.90 0.70	
	A B C D F H J	MIN 14.95 10.00 4.40 0.75 3.10 3.70 0.50 13.4	MAX 15.05 10.10 4.60 0.90 3.30 3.90 0.70 13.6	
	A B C D F H J K	MIN 14.95 10.00 4.40 0.75 3.10 3.70 0.50 13.4 1.10	MAX 15.05 10.10 4.60 0.90 3.30 3.90 0.70 13.6 1.30	
	A B C D F H J K L	MIN 14.95 10.00 4.40 0.75 3.10 3.70 0.50 13.4 1.10 5.00	MAX 15.05 10.10 4.60 0.90 3.30 3.90 0.70 13.6 1.30 5.20	
	A B C D F H J K L N Q	MIN 14.95 10.00 4.40 0.75 3.10 3.70 0.50 13.4 1.10 5.00 2.70	MAX 15.05 10.10 4.60 0.90 3.30 3.90 0.70 13.6 1.30 5.20 2.90	
	A B C D F H J K L	MIN 14.95 10.00 4.40 0.75 3.10 3.70 0.50 13.4 1.10 5.00	MAX 15.05 10.10 4.60 0.90 3.30 3.90 0.70 13.6 1.30 5.20	

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### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =0.25mA	600			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =0.28mA	2.5	3	3.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =3.4A;Tj=25°C V <sub>GS</sub> = 10V; I <sub>D</sub> =3.4A; Tj=150°C		0.41 1.05	0.46	Ω
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V			±100	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0V;Tj=25°C V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0V; Tj=150°C		10	1	μА
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =3.4A, V <sub>GS</sub> = 0 V		0.9		V



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